

# **Notice of References Cited**

Application/Control No.

09/103,873

Applicant(s)/Patent Under  
Reexamination  
NAGANO ET AL.

Examin r

José R. Díaz

Art Unit

2815

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## **U.S. PATENT DOCUMENTS**

*		DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	DOCUMENT SOURCE **	
							APS	OTHER
<input type="checkbox"/>	A	5,608,251	Mar. 1997	Konuma et al.	257	337	<input checked="" type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	B	5,459,353	Oct. 1995	Kanazawa	257	751	<input checked="" type="checkbox"/>	<input type="checkbox"/>
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## **FOREIGN PATENT DOCUMENTS**

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## **NON-PATENT DOCUMENTS**

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\*A copy of this reference is not being furnished with this Office action. (See Manual of Patent Examining Procedure, Section 707.05(a).)

\*\*APS encompasses any electronic search i.e. text, image, and Commercial Databases.

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PTO-892 (Rev. 03-98)

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Part of Paper No. 8